

## METHOD OF FORMING SILICON CARBIDE FILMS

### Abstract of the Disclosure

To deposit silicon onto a substrate, there is introduced into a reaction zone a gas including source gases of silicon, carbon, nitrogen and an inert gas. An electric field is generated using low and high frequency RF power to produce a plasma discharge in the reaction zone to cause the deposition. The average power on the substrate is substantially constant. A ratio of low frequency RF power to total RF power is less than about 0.5.

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